

Si Photo Diode Chip--ORT-2124PD

1. Scope:

- The specification applies to NIP silicon photo diode chips.
- Type: ORT-2124PD

2. Structure:

- NIP planar type.
- Top (Cathode) Side: aluminum (Al) alloy.
- Back (Anode) Side: silver (Ag) alloy.

3. Size: (24mil×24mil)

- Chip size : $(600\mu\text{m} \times 600\mu\text{m}) \pm 40\mu\text{m}$
- Chip thickness : $280\mu\text{m} \pm 20\mu\text{m}$
- Active area : $(460\mu\text{m} \times 460\mu\text{m}) \pm 20\mu\text{m}$
- Pad size : $(120\mu\text{m} \times 120\mu\text{m}) \pm 10\mu\text{m}$
- Pattern drawing: per fig. 1

4. Electro-Optical Characteristics:

($T_a=+25^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F=10\text{mA}, H=0$	0.5		1.3	V
Reverse Breakdown voltage	V_{BR}	$I_R=100\mu\text{A}, H=0$	35			V
Reverse Dark Current	I_D	$V_R=10\text{V}, H=0$			10	nA
Light Current	I_L	$V_R=5\text{V}, \text{Has } 1\text{mw}/\text{cm}^2, @ 940\text{nm}$		9		μA
Peak Sensing wavelength	λ_P			940		nm
Junction Capacitance	C_J	$V_R=3\text{V}, F=1\text{MHz}$		3		pF

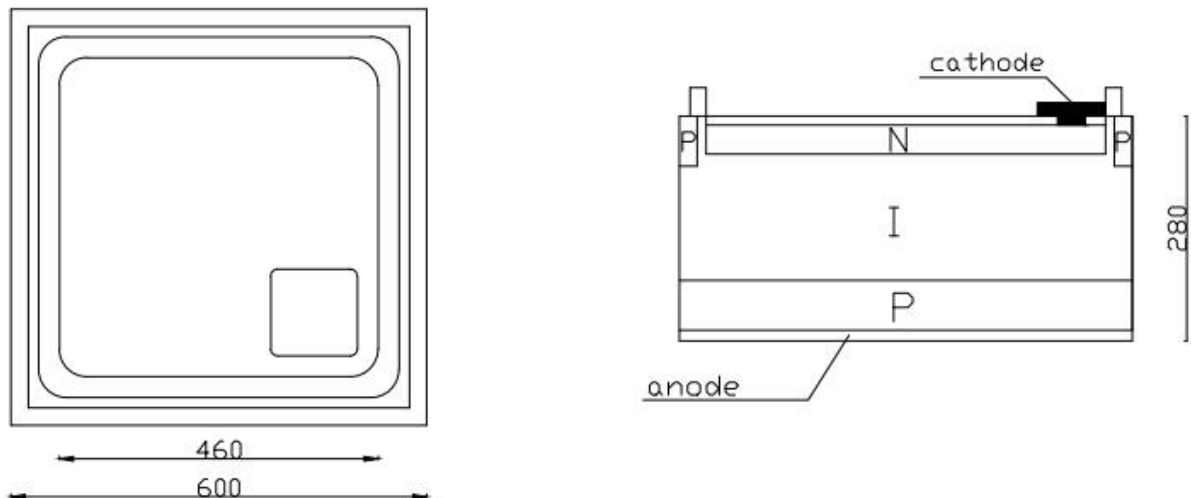


fig.1

5. Spectral Response

